CD74HC125, CD74HCT125

High Speed CMOS Logic
Quad Buffer, Three-State

Features

- **Three-State Outputs**
- **Separate Output Enable Inputs**
- **Fanout (Over Temperature Range)**
  - **Standard Outputs . . . . 10 LSTTL Loads**
  - **Bus Driver Outputs . . . . 15 LSTTL Loads**
- **Wide Operating Temperature Range . . . -55°C to 125°C**
- **Balanced Propagation Delay and Transition Times**
- **Significant Power Reduction Compared to LSTTL Logic ICs**
- **HC Types**
  - **2V to 6V Operation**
  - **High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V**
- **HCT Types**
  - **4.5V to 5.5V Operation**
  - **Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)**
  - **CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}**

Description

The Harris CD74HC125 and CD74HCT125 contain 4 independent three-state buffers, each having its own output enable input, which when "HIGH" puts the output in the high impedance state
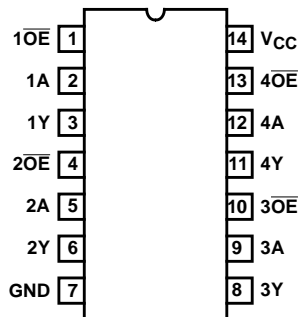
Ordering Information

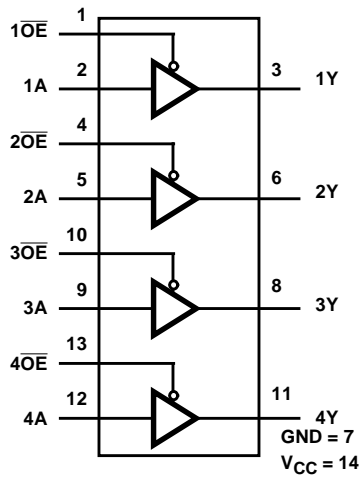| PART NUMBER	TEMP. RANGE (^{o}C)	PACKAGE	PKG. NO.
CD74HC125E	-55 to 125	14 Ld PDIP	E14.3
CD74HCT125E	-55 to 125	14 Ld PDIP	E14.3
CD74HC125M	-55 to 125	14 Ld SOIC	M14.15
CD74HCT125M	-55 to 125	14 Ld SOIC	M14.15

NOTES:

1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.

2. Wafer and die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

Pinout

**CD74HC125, CD74HCT125
(PDIP, SOIC)
TOP VIEW**

```
          _____ ____
1OE   1 |     U    | 14  V_CC
1A    2 |          | 13  4OE
1Y    3 |          | 12  4A
2OE   4 |          | 11  4Y
2A    5 |          | 10  3OE
2Y    6 |          |  9  3A
GND   7 |_____|  8  3Y
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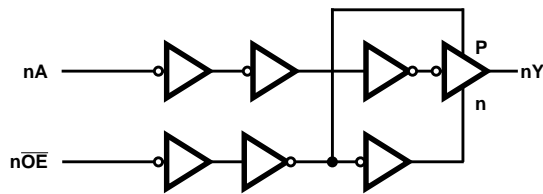
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Functional Diagram

Pin	Signal		Pin	Signal
1	1$\overline{OE}$		3	1Y
2	1A			

(pin connections as shown in diagram)

GND = 7

V_{CC} = 14

TRUTH TABLE

INPUTS		OUTPUTS
nA	nOE	nY
H	L	H
L	L	L
X	H	Z

NOTE:
H = High Voltage Level
L = Low Voltage Level
X = Don't Care
Z = High Impedance, OFF State

Logic Diagram

nA

n$\overline{OE}$

P

n

nY

CD74HC125, CD74HCT125

Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
  For V_I < -0.5V or V_I > V_{CC} + 0.5V . . . . ±20mA
DC Output Diode Current, I_{OK}
  For V_O < -0.5V or V_O > V_{CC} + 0.5V . . . . ±20mA
DC Drain Current, per Output, I_O
  For -0.5V < V_O < V_{CC} + 0.5V . . . . ±35mA
DC Output Source or Sink Current per Output Pin, I_O
  For V_O > -0.5V or V_O < V_{CC} + 0.5V . . . . ±25mA
DC V_{CC} or Ground Current, I_{CC} . . . . ±70mA

Operating Conditions

Temperature Range (T_A) . . . . -55°C to 125°C
Supply Voltage Range, V_{CC}
  HC Types . . . . .2V to 6V
  HCT Types . . . . .4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . 0V to V_{CC}
Input Rise and Fall Time
  2V . . . . 1000ns (Max)
  4.5V. . . . . 500ns (Max)
  6V . . . . 400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 3) θ_{JA} (°C/W)
  PDIP Package   90
  SOIC Package   175
Maximum Junction Temperature . . . . 150°C
Maximum Storage Temperature Range . . . .-65°C to 150°C
Maximum Lead Temperature (Soldering 10s) . . . . 300°C
  (SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

| PARAMETER | SYMBOL | TEST CONDITIONS | | V_{CC} (V) | 25°C | | | -40°C TO 85°C | | -55°C TO 125°C | | UNITS |
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	μA

DC Electrical Specifications   (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS			25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)	V_{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	µA
Three-State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	-	6	-	-	±0.5	-	±5	-	±10	µA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} to GND	0	5.5	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 4)	ΔI_{CC}	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA
Three-State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	-	5.5	-	-	±0.5	-	±5	-	±10	µA

NOTE:

4. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
nA, n$\overline{OE}$	1

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360µA max at 25°C.

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
HC TYPES								
Propagation Delay Time nA to nY	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	100	125	150	ns
			4.5	-	20	25	30	ns
		C_L = 15pF	5	8	-	-	-	ns
		CL = 50pF	6	-	17	21	26	ns
Enable Delay Time	t_{PZL}, t_{PZH}	C_L = 50pF	2	-	125	155	190	ns
			4.5	-	25	31	38	ns
		C_L = 15pF	5	10	-	-	-	ns
		CL = 50pF	6	-	21	26	32	ns
Disable Delay Time	t_{PLZ}, t_{PHZ}	C_L = 50pF	2	-	125	155	190	ns
		C_L = 50pF	4.5	-	25	31	38	ns
		C_L = 15pF	5	10	-	-	-	ns
		C_L = 50pF	6	-	21	26	32	ns
Output Transition Time	t_{TLH}, t_{THL}	C_L = 50pF	2	-	60	75	90	ns
			4.5	-	12	15	18	ns
			6	-	10	13	15	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 5, 6)	C_{PD}	-	5	29	-	-	-	pF
HCT TYPES								
Propagation Delay Time nA to nY	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	25	31	38	ns
		C_L = 15pF	5	10	-	-	-	ns
Output Enable Time	t_{PZL}, t_{PZH}	C_L = 50pF	4.5	-	25	31	38	ns
		C_L = 15pF	5	10	-	-	-	ns
Output Disabling Time	t_{PLZ}, t_{PHZ}	C_L = 50pF	4.5	-	28	35	42	ns
		C_L = 15pF	5	11	-	-	-	ns
Output Transition Times	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	12	15	18	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 5, 6)	C_{PD}	-	5	34	-	-	-	pF

NOTES:

5. C_{PD} is used to determine the dynamic power consumption, per channel.

6. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, f_O = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

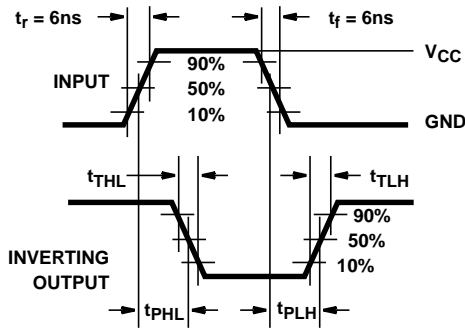## *Test Circuits and Waveforms*

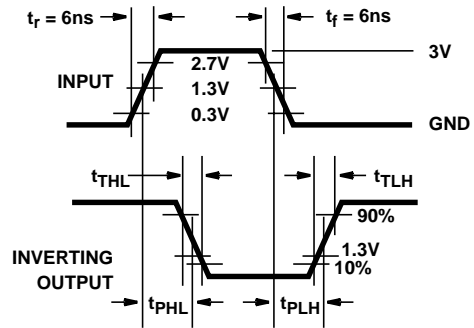**FIGURE 1. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC**

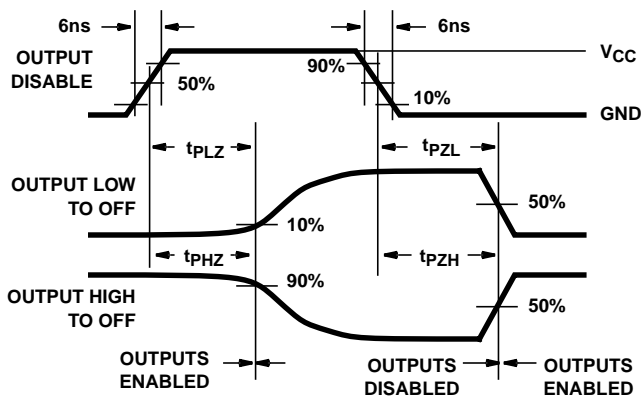**FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC**

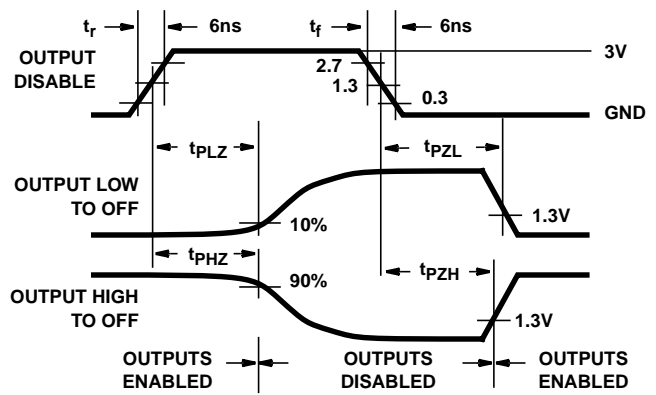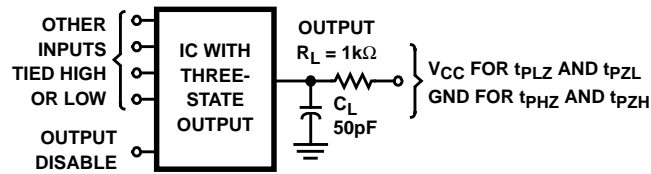**FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM**

FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM

NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output R_L = 1kΩ to V_{CC}, C_L = 50pF.

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

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